

SOT23 N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

Features

• For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q101, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative.

<u>https://www.diodes.com/quality/product-definitions/</u>

PARTMARKING DETAIL – SA

Absolute Maximum Ratings



PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V _{DS}	100	V
Drain-Gate Voltage	V _{DGR}	100	V
Continuous Drain Current at T _{amb} =25°C	I _D	170	mA
Pulsed Drain Current	I _{DM}	680	mA
Gate-Source Voltage	V _{GS}	± 20	V
Peak Gate-Source Voltage	V _{GSM}	± 20	V
Power Dissipation at T _{amb} =25°C	P _{tot}	360	mW
Operating and Storage Temperature Range	T _j :T _{stg}	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

PARAMETER	SYMBOL	MIN.	MIN.	MAX.	UNIT	CONDITIONS.	
Drain-Source Breakdown Voltage	BV _{DSS}	100			V	I _D =0.25mA, V _{GS} =0V	
Gate-Source Threshold Voltage	V _{GS(th)}	0.8	2.2	2.8	V	I _D =1mA, V _{DS} = V _{GS}	
Gate-Body Leakage	I _{GSS}		10	50	nA	$V_{GS}=\pm 20V, V_{DS}=0V$	
Zero Gate Voltage Drain Current	I _{DSS}		1 2	15 60 10	μΑ μΑ nA	V_{DS} =100V, V_{GS} =0V V_{DS} =100V, V_{GS} =0V, T=125°C(2) V_{DS} =20V, V_{GS} =0V	
Static Drain-Source On-State Resistance (1)	R _{DS(on)}		5	6	Ω	V _{GS} =10V, I _D =100mA	
Forward Transconductance(1)(2)	9 _{fs}	80	120		mS	V _{DS} =25V, I _D =100mA	
Input Capacitance (2)	C _{iss}			20	pF		
Common Source Output Capacitance (2)	C _{oss}			9	pF	V _{DS} =25V, V _{GS} =0V, f=1MHz	
Reverse Transfer Capacitance (2)	C _{rss}			4	pF		
Turn-On Delay Time (2)(3)	t _{d(on)}		10		ns		
Rise Time (2)(3)	t _r		10		ns	$V_{DD} \approx 30V, I_{D} = 280 mA$	
Turn-Off Delay Time (2)(3)	t _{d(off)}		15		ns		
Fall Time (2)(3)	t _f		25		ns		

(1) Measured under pulsed conditions. Width=300µs. Duty cycle ≤2% (2) Sample test.

(3) Switching times measured with 50Ω source impedance and <5ns rise time on a pulse generator

For typical characteristics graphs see ZVN3310F datasheet.



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